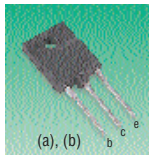


High Voltage Power Transistors –
V_{CEO} 150V to 800V — continued

CRT Deflection Transistors – Isolated Packages



(a) ISOWATT218
Lead spacing = 5.45
Isolation voltage = 4000V dc
(b) TO-3P (IS)
Isolation voltage = 2500V dc

I _C (AV) A	V _{CEO} V	V _{CB0} V	V _{CE} (sat) V	@ I _C A	P _{tot} @ 25°C W	Package	Mfr.	Mfrs. List No.
5.0	700	1500	1.5	3.0	50	a	ST	BUH315
6.0	600	1500	5.0	4.0	50	b	TOSH	2SC3884A
6.0	600	1500	5.0	5.0	50	b	TOSH	2SD2125
7.0	600	1500	5.0	5.0	50	b	TOSH	2SC4757
8.0	600	1500	5.0	6.0	50	b	TOSH	2SC3886A
8.0	700	1700	1.5	5.0	60	a	ST	BUH517
8.0	1500**	1500	1.0	4.5	50	b	TOSH	S2000N
10.0	700	1500	1.5	7.0	65	a	ST	BUH715

**Specified as V_{CEs}

SD157

Mfrs. List No.	Order Code	1+	25+	100+	500+	1K+
BUH315	.233-948					
BUH517	.233-973					
BUH715	.233-985 †					
2SD2125	.572-603					
S2000N	.572-615					
2SC4757	.572-639					
2SC3886A	.572-652					
2SC3884A	.572-664					

† Available until stocks are exhausted

NPN Lighting Transistors

Philips Semiconductors



TO-220AB

SD471

V _{CE} V	I _C A	Mfrs. List No.	Order Code	1+	25+	100+	500+	1K+
700	4	BUJ103A	.316-5188					
700	10	BUJ106A	.316-5462					
850	6	BUJ204A	.316-5190					
1000	5	BUJ303A	.316-5206					
1200	6	BUJ403A	.316-5218					

SMPS and Lighting Transistors

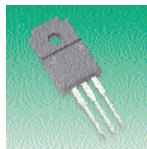
Philips Semiconductors



SOD-82



TO-220AB



SOT-186

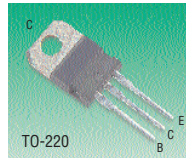
V _{CESM} (V)	I _C (DC) (A)	I _C (SAT) (A)	t _r (max.) (μs)	LEADED PACKAGES		
				SOT82	TO220AB (SOT78)	SOT186
800	0.5	—	0.28	BUX86P		
800	2	1	0.4		BUX84	
850	5	3	0.8		BUT11	
1000	0.5	—	0.28	BUX87P		
1000	2	1	0.4		BUX85	BUX85F
1000	5	2.5	0.8		BUT11A	
1000	6	4	0.8			BUT18AF
1000	8	5	0.8		BUT12A	

SD44

Mfrs. List No.	Order Code	1+	25+	100+	500+	1K+
BUT11	.359-646					
BUT11A	.359-658					
BUT12A	.359-660					
BUT18AF	.681-880					
BUX84	.359-877					
BUX85	.359-889					
BUX85F	.681-969					
BUX86P	.663-890					
BUX87P	.663-906					

Electronic Lamp Ballast Transistors

ON Semiconductor



TO-220

NPN bipolar power transistors optimised for use in energy-saving compact fluorescent, industrial and halogen lamp ballasts.

◊ Integrated collector-emitter diode and anti-saturation network

I _C cont. (max.) A	I _C (op) operating A	V _{CEO} (min.) V	V _{CEs} (min.) V	h _{FE} min. @ I _C (op) V _{CE} = 1V 8 (typ.)	Inductive Switching T _{si} (max.) μs	P _D @ 25°C W	Mfrs. List No.
4	2	500	800	8 (typ.)	2.5	50	BUH50
5	2	400	700	7	3.8	75	BUL45
5	2	400	700	10	2.25	75	◊ BUL45D2
5	2	450	1000	6	2.5	75	MJE18004
6	3	400	700	8	3.8	100	BUL146
6	3	450	1000	6	3.2	100	MJE18006
10	—	400	700	15	6.0	100	BUH100

SD281

Mfrs. List No.	Order Code	1+	25+	100+	250+	1K+
BUH50	.681-568					
BUH100	.334-3480					
BUL45	.681-593					
BUL45D2	.931-329					
BUL146	.681-600					
MJE18004	.681-623					
MJE18006	.681-635					

Darlington Transistors

SOT-23 Darlington NPN

Philips Semiconductors

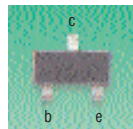


V _{CEO} max. V	V _{CB0} max. V	I _C (av) max. A	h _{FE} min.	I _C @ A	Device Marking	Package	Mfrs. List No.
60	80	0.5	20000	0.1	FGp	SOT-23	BCV47

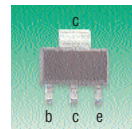
SD76

Order Multiple=5	Mfrs. List No.	Order Code	5+	100+	200+	500+	1K+
BCV47		.302-3333					

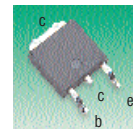
SOT-23, SOT-223 and D-pak Darlington



(a) SOT-23



(b) SOT-223



(c) TO-252/D-pak
H = 2.55, W = 6.8, D = 10.5

V _{CEO} max V	V _{CB0} max V	I _C (dc) max. A	h _{FE} min @	I _C mA	Device Marking	Package	Mfr.	Mfrs. List No.
30	30	0.3	10000	10.0	1M	a	FCH	MMBTA13 —
60	80	0.3	1000	0.5	4J	a	ZET	FM3T38A —
60	80	0.3	4000	0.5	5J	a	ZET	FM3T38B —
60	80	0.3	10000	0.5	7J	a	ZET	FM3T38C —
100	—	8.0	1000	4.0	—	c	ON	MJD122 MJD127 —
120	140	1.5	5000	0.5	—	b	ZET	FZT605 —
120	140	2.0	3000	1.0	—	b	ZET	— FZT705
140	160	2.0	2000	0.5	—	b	ZET	FZT600 —

SD177

Order Multiple=5	Mfrs. List No.	Order Code	5+	100+	200+	500+	1K+
FM3T38A		.302-6980					
FM3T38B		.302-6991					
FM3T38C		.516-934					
FZT600		.707-806					
FZT605		.538-279					
FZT705		.538-280					
MJD122		.708-550					
MJD127		.708-562					
MMBTA13		.743-021					